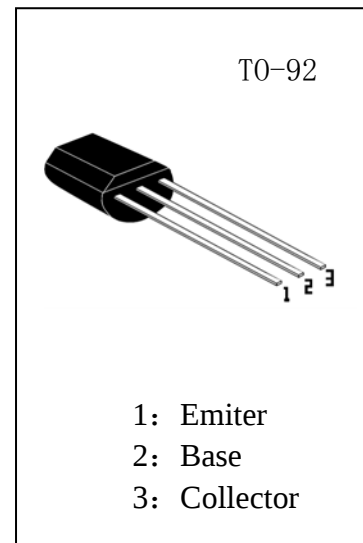


GENERAL PURPOSE TRANSISTOR

- $V_{ce0}=40V$
- $P_c=625mW$
- 与 2N3906 对管

极限参数(Absolute Maximum Ratings) $T_a=25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	60	V
Collector-Emitter Voltage	V_{ceo}	40	V
Emitter-Base Voltage	V_{ebo}	6	V
Collector Current	I_c	200	mA
Collector Dissipation	P_c	625	m W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$


电性能(Electrical Characteristic) $T_a=25^{\circ}C$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=10\mu A$ $I_e=0$	60			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=1mA$ $I_b=0$	40			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=10\mu A$ $I_c=0$	6			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=50V$, $I_e=0$			100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=3V$, $I_c=0$			50	nA
I_{cex}	Collector Cutoff Current	$V_{ce}=30V$, $V_{eb}=3V$			50	nA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c=10mA$, $I_b=1mA$			0.2	V
$V_{ce(sat)2}$	Collector-Emitter Saturation Voltage	$I_c=50mA$, $I_b=5mA$			0.3	V
$V_{be(sat)1}$	Base-Emitter Saturation Voltage	$I_c=10mA$, $I_b=1mA$			0.85	V
$V_{be(sat)2}$	Base-Emitter Saturation Voltage	$I_c=50mA$, $I_b=5mA$			0.95	V
Hfe1	DC Current Gain	$V_{ce}=1V$, $I_c=0.1mA$	40			
Hfe2	DC Current Gain	$V_{ce}=1V$, $I_c=1mA$	70			
Hfe3	DC Current Gain	$V_{ce}=1V$, $I_c=10mA$	80		400	
Hfe4	DC Current Gain	$V_{ce}=1V$, $I_c=50mA$	60			
Hfe5	DC Current Gain	$V_{ce}=1V$, $I_c=100mA$	30			
Cob	Output Capacitance	$V_{cb}=5V$, $I_e=0$, $f=1MHz$			4	PF
fT	Current Gain-Bandwidth product	$V_{ce}=20V$, $I_c=10mA$,	300			MHz

CLASS	B	C	D	E
Hfe3	80-100	100-200	200-300	300-400